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Applicant : King Jien Chui  
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**Remarks/Arguments**

3 Examiner Ms. Joannie Garcia is thanked for the thorough Office  
4 Action.

5

**In the Claims**

7 Parent claim 1 has been amended: to add – at least a portion  
8 of – before “the doped depletion” at line 10 of claim 1; and to add – directly –  
9 before “beneath” at line 11 of claim 1. No new matter has been entered. For  
10 support, please see Fig. 3A, for example. Applicants urge that the addition of “at  
11 least a portion of” broadens claim 1. Applicants urge that the addition of “directly”  
12 simply makes explicit what was implicit in view of the specification and drawings  
13 as filed and does not narrow claim 1.

14 Parent claim 1 has been amended to add – and – after  
15 subparagraph b). This amendment corrects an inadvertent editorial error and is  
16 not believed to narrow the scope of claim 1.

17 Claim 2 is amended. For support see fig 3A. See Spec. p. 14.

18 Claim 4 has been amended to replace “region” with – regions –  
19 as requested by the Examiner to overcome the Objection to claim 4. This  
20 amendment is not believed to narrow the scope of claim 4.

21 Claim 7 has been amended to: delete the slash (/) between the  
22 words “source” and “drain” and replace it with the word – and – at line 2 of claim  
23 7 for clarity. These amendments are not believed to narrow the scope of claim 7.

24 Claim 9 is amended to add “the doped depletion regions are  
25 directly beneath and separated from said LDD regions.”. for support see Figure  
26 2A and 2B.

27

28

29 Claim 21 has further been amended by replacing “implant” with

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1 -- implantation -- as requested by the Examiner to overcome the objection to  
2 claim 21. This amendment is not believed to narrow the scope of claim 21.

3 Parent claim 23 has been amended in the manner requested by  
4 the Examiner to overcome the objections to claim 23. Further: the slash (/) has  
5 been removed between the words "source" and "drain" and replace with – and –  
6 at line 7 of claim 23 for clarity; and the word – and – has been added before step  
7 c) as an editorial amendment. These amendments are not believed to narrow the  
8 scope of claim 23.

9 Claim 25 has been amended to: delete the slash (/) between the  
10 words "source" and "drain" and replace with – and – at line 2 of claim 25 for  
11 clarity; and add – about – after "between" at each instance. These amendments  
12 are not believed to narrow the scope of claim 25.

13 Claim 38 has been amended to add -- and -- after line 3. This  
14 amendment is not believed to narrow the scope of claim 38.

15 **New claims**

16 Claims 41 to 43 are new and have been added to better  
17 encompass the full scope and breadth of the invention notwithstanding the  
18 patentability of the original claims.

19 Claim 41 depends from independent claim 1.

20 Claim 42 depends from independent claim 23.

21 Claim 43 is an independent claim and comprises the limitations  
22 of independent claim 1 and allowable claim 9 (thus claim 43 is now allowable).

23

24 No new matter has been added in any of the above claim  
25 amendments and in no case do these amendments narrow the scope of the  
26 respective claims and they do not invoke FESTO related amendments.

27

28 **Objection to the claims for Informalities**

29 The claims are amended to correct the informalities kindly point  
30 out the examiner.

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2 **CLAIM REJECTIONS:**

3

4 **Rejection Of Claims 1, 2, 7, 8 and 14 Under 35 U.S.C. § 102(b) as being**  
5 **anticipated by Burr (US Patent Publication 2003/0178698 A1)**

6

7 The rejection of claims 1, 2, 7, 8 and 14 under 35 U.S.C. §  
8 102(b) as being anticipated by Burr (US Patent Publication 2003/0178698 A1)  
9 (the '698 Burr Publication) is acknowledged. Reconsideration and withdraw is  
10 respectfully requested in view of the amendments.

11 Applicant urges that amended Parent claim 1 is allowable for  
12 the following reasons.

13 **Parent Claim 1 is allowable**

14 Amended Claim 1 is not anticipated *nor obvious* in view of Burr  
15 because Burr does not disclose or fairly teach claim 1's limitations of, *inter alia*:

16  
17 **at least a portion of the doped depletion regions are directly**  
18 **beneath and separated from said source and drain regions;**  
19

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1 Parent claim 1 states:

1. (CURRENTLY AMENDED) A method of forming a semiconductor device comprising:  
  
a) forming a gate structure over a substrate being doped with a first conductivity type impurity;  
b) performing a doped depletion region implantation by implanting ions being a second conductive type into the substrate to form doped depletion regions; and  
c) performing a S/D implantation by implanting ions being the second conductivity type into the substrate to form source and drain regions adjacent to said gate structure; **at least a portion of the doped depletion regions are directly beneath and separated from said source and drain regions;**  
(1) said doped depletion regions having an impurity concentration and thickness so that said doped depletion regions are depleted due to a built-in potential created between said doped depletion regions and said substrate;  
said doped depletion regions having an impurity concentration so that a built-in junction potential between said doped depletion regions and said substrate forms depletion regions in the substrate between the source and drain regions and the doped depletion regions;  
said depletion regions have a net impurity concentration of the first conductivity type.

2

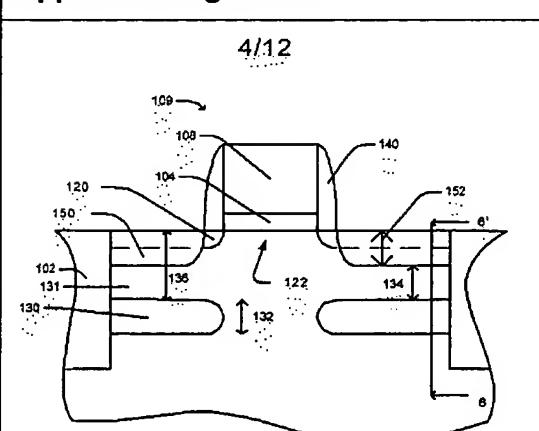
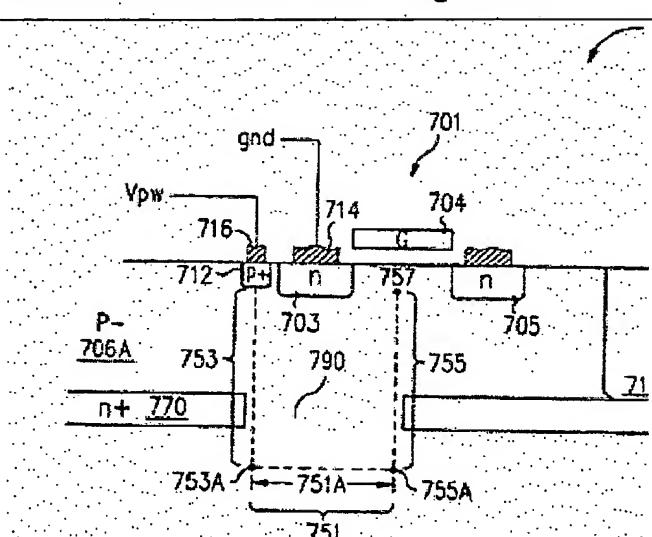
3

4              Applicants repeat their previous relevant arguments as to the  
5        '698 Burr Patent Publication as to amended claim 1 and further, Parent claim 1  
6        includes the limitation, inter alia, "**at least a portion of the doped depletion**  
7        **regions are directly beneath and separated from said source and drain**  
8        **regions;**". This limitation is not shown or fairly described in Burr as evidenced by  
9        Table A showing Applicant's figure 3A and Burr's figure 7A:  
10

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1 Table A

Applicant's figure 3A	US 2003-078698 Burr et al. -figure 7A
 <p>FIGURE 3A</p>	 <p>FIG. 7A</p>

2

3

4 Thus Fig. 3A shows that at least a portion of the doped  
 5 depletion regions 130 are directly beneath and separated from said source  
 6 region 150 and said drain region 150. In contrast, Burr figure 7A shows that no  
 7 portion of perforated Buried N-well (N+) 770 is directly beneath both the  
 8 source and drain regions 703 and 705. Burr figure 7A clearly shows there is no  
 9 perforated Buried N-well (N+) 770 beneath the source/drain region 703. In fact, in  
 10 Figure 7A, Burr teaches away from this limitation by showing only the substrate  
 11 (not buried N+ well 770) beneath the source/drain 703. See Figure 7A; See Burr  
 12 para 164. A Key to Burr's invention is the opening below the S/D that provide a  
 13 longer resistance page. See Burr Abstract, col. para 164.

14

15

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1                   The instant office action posits the follow:

2                   performing a doped depletion implantation region by implanting ions being a  
3                   second conductivity type to the substrate to form doped depletion regions 770  
4                   beneath and separated from source/drain regions 703 705 (Figure 7 A and  
5                   Paragraphs 0161, and 0164),  
6

7                   However, as shown above in amended claim 1 and table A, Burr  
8                   (Figure 7 A and Paragraphs 0161, and 0164) do not teach applicant's claimed  
9                   doped depletion regions 130 are directly beneath and separated from said  
10                  source region 150 and said drain region 150. Moreover, Burr teaches a different  
11                  method to form the buried N+ well 770. As noted above there is no motivation to  
12                  change Burr since a key to Burr's invention is the opening below the S/D that  
13                  provide a longer resistance page. See Burr Abstract, col. para 164. Furthermore  
14                  there is no motivation to modify Burr to meet applicant's claim 1 since Burr solves  
15                  a different problem than the invention.

16  
17                  Therefore claim 1 is allowable.  
18

19                  **Amended Claim 2 is non-obvious**

20                  Amended claim 2 states:

21  
22                  2. (CURRENTLY AMENDED) The method of claim 1 wherein said doped  
23                  depletion regions are not formed directly under said gate structure.

24  
25                  As discussed above, Burr teaches against this limitation. In  
26                  contrast to claim 2, Burr fig. 7A forms buried N+ well 770 directly under the gate.

27  
28                  Claims 2, 7, 8 and 14 depend from claim 1 and therefore they  
29                  are also allowable.

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2 **Rejection of claims 12, 13, 15, 18 to 21 and 23 to 25 under 35 U.S.C. § 103(a)**  
3 **as being unpatentable over Burr (US Patent Publication 2003/0178698 A1)**  
4 **as applied to claims 1, 2, 7, 8 and 14 above and further in view of Bae et al.**  
5 **al (US Patent Publication 2004/0075143 A1).**

6

7                 The rejection of claims 12, 13, 15, 18 to 21 and 23 to 25 under  
8 35 U.S.C. § 103(a) as being unpatentable over Burr (US Patent Publication  
9 2003/0178698 A1) (the '698 Burr Publication) as applied to claims 1, 2 ,7. 8 and  
10 14 above and further in view of Bae et al. al (US Patent Publication  
11 2004/0075143 A1) (the '143 Bae Publication) is acknowledged. Reconsideration  
12 and withdrawal of the rejection is respectfully requested in view of the  
13 amendments.

14

15 **Claims 12 13 15 and 18 to 21 depend from amended parent claim 1**

16

17                 Claims 12 13 15 and 18 to 21 depend from amended parent  
18 claim 1 are should be allowable for the reasons discussed above under the  
19 102(b) rejection of claims 1, 2, 7, 8 and 14.

20

21                 This amendment is not a concession that the previous versions  
22 of claims are not allowable. This amendment made to accelerate the allowance  
23 of claims. Applicant still maintains that previous claim 1 and it's depend claims  
24 are allowable for the reasons stated in the previous responses to office actions.

25

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1 Parent Claim 23 is allowable

2 Parent claim 23 states:

23. (CURRENTLY AMENDED) A method of forming a semiconductor device comprising:

- a) forming a gate structure over a substrate being doped with a first conductivity type impurity;
- b) performing a doped depletion region implantation by implanting ions being a second conductivity type to the substrate to form doped depletion regions beneath and separated from said source[/] and drain regions;
  - (1) said doped depletion regions have an impurity concentration and thickness so that said doped depletion regions are depleted due to a built-in potential created between said doped depletion regions and said substrate; and
- c) performing a S/D implantation by implanting ions being the second conductivity type into the substrate to form said source and drain regions adjacent to said gate structure;
  - (1) said substrate between said source and drain regions and said doped depletion regions has a concentration of a first type impurity between 1E16 to 1E18 atom/cc;  
**said doped depletion regions have an impurity concentration so that the built-in potential between said doped depletion regions and said substrate forms depletion regions in the substrate between the source and drain regions and the doped depletion region regions; said depletion regions have a net impurity concentration of the first conductivity type; said depletion regions have a net impurity concentration between 1E16 to 1E18 atom/cc.**

3

4

5 Parent claim 23 contains at least the subject matter limitations  
6 of claim 1 (without the addition of – at least a portion of – and – directly – added  
7 in the instant Response) and the limitations of allowable claim 4 (**bolded**  
8 **above**).

9

10 Therefore claim 23 is allowable.

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2 Dependent Claims 24 to 27 are allowable

3                   Dependent claims 24 to 27 depend from claim 23 which, by the  
4 Examiner's statement of allowability of dependent claim 4 and Applicants'  
5 arguments above, is allowable and hence claims 24 to 27 are allowable.

6

7 Dependent Claims 24 is (further) allowable

8                   Dependent Claim 24 is (further) allowable because it includes  
9 the limitation "wherein said doped depletion regions are not formed under said  
10 gate structure." See Table A above which clearly demonstrates that Burr lacks  
11 this limitation and the '143 Bae Patent Publication does not cure this shortcoming  
12 under 103(a). Also, because of the reasons given in the previous office action.

13

14                  Thus claims 12, 13, 15, 18 to 21 and 23 to 25 are patentably  
15 distinguishable under 35 U.S.C. § 103(a) over Burr as applied to claims 1, 2, 7, 8  
16 and 14 above, and further in view of Bae for the above reasoning/arguments and  
17 further because, inter alia: the prior art lack a suggestion that the reference  
18 should be modified in a manner required to meet the claims; Burr is a poor  
19 reference; the Examiner misunderstood Burr; the invention is contrary to the  
20 teaching of the prior art—that is, the invention goes against the grain of what the  
21 prior art teaches; the Examiner has made a strained interpretation of the  
22 reference that could be made only be hindsight; the Examiner has not presented  
23 a convincing line of reasoning as to why the claimed subject matter as a whole,  
24 including its differences over the prior art, would have been obvious; and the  
25 reference takes a difference approach.

26

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1 **The combination of Burr and Bae is improper**

2

3                Yet further, the combination of Burr and Bae is improper for the  
4 following reasons. Burr and Bae are unrelated, solve different problems, use  
5 different solutions and have no process steps in common. The combination is  
6 Unsuggested: The prior art references do not contain any suggestions (express  
7 or implied) that they be combined, or that they be combined in the manner  
8 suggested. The references are individually Complete: Each reference is  
9 complete and functional in itself, so there would be no reason to use parts from  
10 or add or substitute parts to any reference.

11 Therefore combination is improper.

12

13                Even if combined, the references do not meet or suggest the  
14 applicant's claims.

15

16                The dependent claims depend from non-obvious parent claims  
17 and are therefore non-obvious. As described above, the parent claims are non-  
18 obvious over the references.

19

20                **NEW CLAIMS**

21 **New claim 41 is non-obvious.**

22                Claim 41 states:

23                41. (NEW) The method of claim 1, further comprising a channel region in  
24                said substrate under said gate structure; wherein said heavily  
25                doped depletion regions are not directly beneath said channel  
26                region.

27 As discussed above, Burr teaches against claim 41.

28

29 **Claim 42 is non-obvious**

30

31                Claim 42 depends from independent claim 23.

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1        42. (NEW) The method of claim 23, wherein at least a portion of the doped  
2            depletion regions are directly beneath and separated from said  
3            source and drain regions.

4  
5            Burr teaches against having depletion regions under both the  
6            source and drain. See Burr fig. 7A.

7

8        Claim 43 is allowable

9            Claim 43 is an independent claim and comprises the limitations  
10          of independent claim 1 and allowable claim 9 (thus claim 43 is now allowable).

11

12

13        ALLOWABLE SUBJECT MATTER

14

15            The allowance of claims 38 to 40 is gratefully acknowledged.

16

17            The objection to claims 4\* to 6, 9 to 11, 16, 17, 22, 26, 27 and  
18          37 as being dependent upon a rejected base claims, but allowable if rewritten in  
19          independent form is gratefully acknowledged. [\*Please see the argument above  
20          for the allowability of independent claim 23 as it now includes, *inter alia*, the  
21          limitations of claim 1 and claim 4.]

22

23            Applicant requests that the rewriting of objected to claims 4, 9 to  
24          11, 16, 17 and 22 be held in abeyance pending the final determination of the  
25          allowability of their parent claim 1. Applicant requests that the rewriting of  
26          objected to claims 26 and 37 be held in abeyance pending the final determination  
27          of the allowability of their parent claim 23.

28

29        CONCLUSION

30

31            It is believed that all the pending claims have been addressed.  
32          However, the absence of a reply to a specific rejection, issue or comment does

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1 not signify agreement with or concession of that rejection, issue or comment. In  
2 addition, because the arguments made above may not be exhaustive, there may  
3 be reasons for patentability of any or all pending claims (or other claims) that  
4 have not been expressed. Finally, nothing in this paper should be construed as an  
5 intent to concede any issue with regard to any claim, except as specifically stated  
6 in this paper. and the amendment of any claim does not necessarily signify  
7 concession of the unpatentability of the claim prior to its amendment.

8 In conclusion, reconsideration and withdrawal of the rejections  
9 are respectfully requested. Allowance of all claims is requested. Issuance of the  
10 application is requested.

11 It is requested that the Examiner telephone the undersigned  
12 attorney at (215) 670-2455 should there be anyway that we could help to place  
13 this Application in condition for Allowance.

14

15 **Charge to Deposit Account**

16

17 The Commissioner is hereby authorized to apply any fees or  
18 credits in this case, which are not already covered by check or credit card, to  
19 Deposit Account No. 502018 referencing this attorney docket. The Commissioner  
20 is also authorized to charge any additional fee under 37 CFR §1.16 and 1.17 to  
21 this Deposit Account.

22

23 Respectfully submitted,

24 William J. Stoffel REG # 39,390/

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33

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